SKKT 330, SKKH 330

THYRISTOR BRIDGE,SCR,BRIDGE

查询"SKKH330/08E"供应商

SEMIPACK® 3

Thyristor / Diode Modules

SKKH 330

SKKT 330

Features

- Heat transfer through aluminium nitride ceramic isolated metal baseplate
- Precious metal pressure contacts for high reliability
- Thyristor with amplifying gate
- UL recognized, file no. E 63 532

Typical Applications

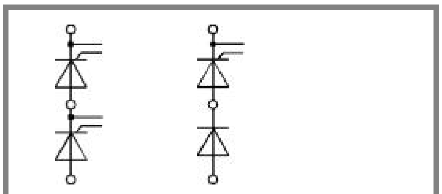
- DC motor control (e. g. for machine tools)
- Temperature control (e. g. for ovens, chemical processes)
- Professional light dimming (studios, theaters)

1) See the assembly instructions

2) The screws must be lubricated

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 510 A (maximum value for continuous operation) I_{TAV} = 330 A (sin. 180; T_c = 80 °C)		
900	800	SKKT 330/08E	SKKH 330/08E	
1300	1200	SKKT 330/12E	SKKH 330/12E	
1700	1600	SKKT 330/16E	SKKH 330/16E	
1900	1800	SKKT 330/18E	SKKH 330/18E	

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 85 (100) °C;	305 (225)	A
I_D	P16/200F; T_a = 35 °C; B2 / B6	520 / 650	A
I_{RMS}	P16/200F; T_a = 35 °C; W1 / W3	585 / 3 * 485	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	9500	A
	T_{vj} = 130 °C; 10 ms	8000	A
i²t	T_{vj} = 25 °C; 8,3 ... 10 ms	451000	A²s
	T_{vj} = 130 °C; 8,3 ... 10 ms	320000	A²s
V_T	T_{vj} = 25 °C; I_T = 750 A	max. 1,4	V
$V_{T(TO)}$	T_{vj} = 130 °C	max. 0,8	V
r_T	T_{vj} = 130 °C	max. 0,6	mΩ
I_{DD}; I_{RD}	T_{vj} = 130 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 50	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 130 °C	max. 250	A/µs
$(dv/dt)_{cr}$	T_{vj} = 130 °C	max. 1000	V/µs
t_q	T_{vj} = 130 °C ,	50 ... 150	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 500	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 2000	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 3	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 200	mA
V_{GD}	T_{vj} = 130 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 130 °C; d.c.	max. 10	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,11 / 0,055	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,116 / 0,058	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,13 / 0,065	K/W
$R_{th(c-s)}$	per thyristor / per module	0,04 / 0,02	K/W
T_{vj}		- 40 ... + 130	°C
T_{stg}		- 40 ... + 130	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 % 1)	Nm
M_t	to terminals	9 ± 15 % 2)	Nm
a		5 * 9,81	m/s²
m	approx.	600	g
Case	SKKT	A 73b	
	SKKH	A 76b	



SKKT SKKH

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RECTIFIER,DIODE,THYRISTOR,MODULE

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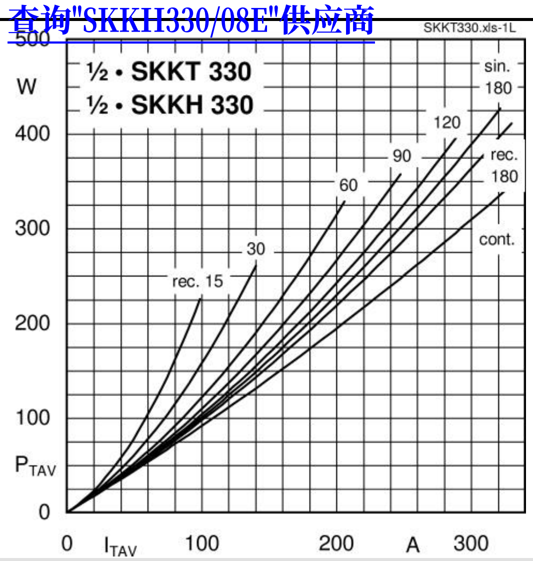

Fig. 1L Power dissipation per thyristor vs. on-state current

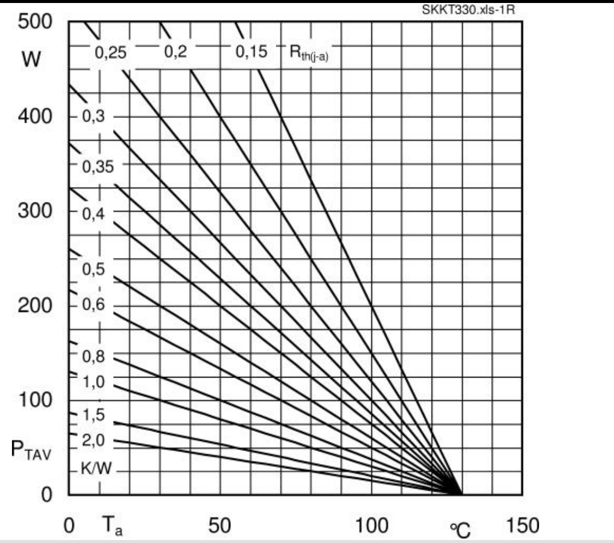

Fig. 1R Power dissipation per thyristor vs. ambient temp.

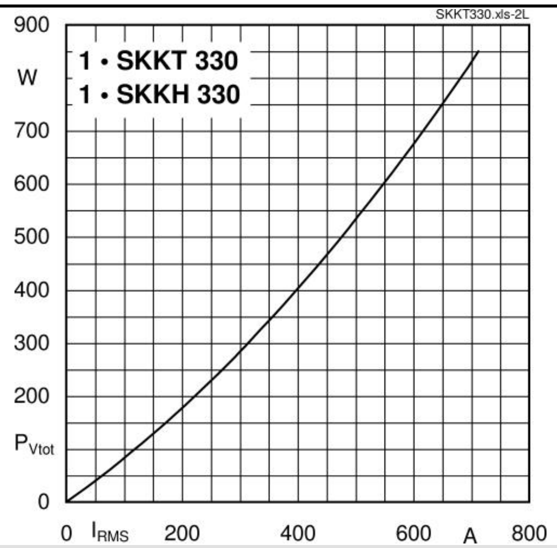

Fig. 2L Power dissipation per module vs. rms current

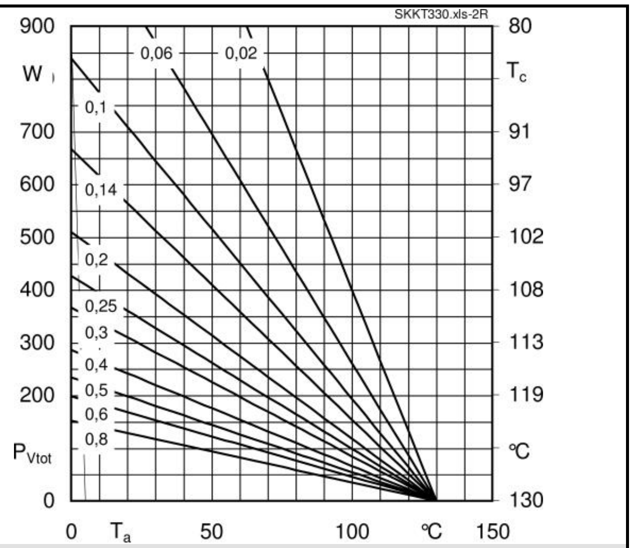

Fig. 2R Power dissipation per module vs. case temp.

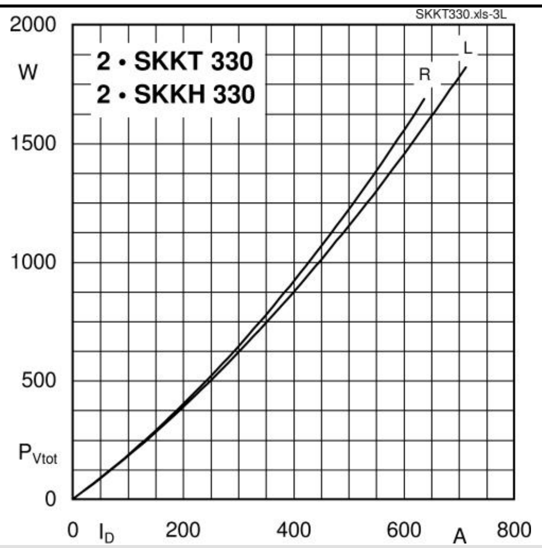

Fig. 3L Power dissipation of two modules vs. direct current

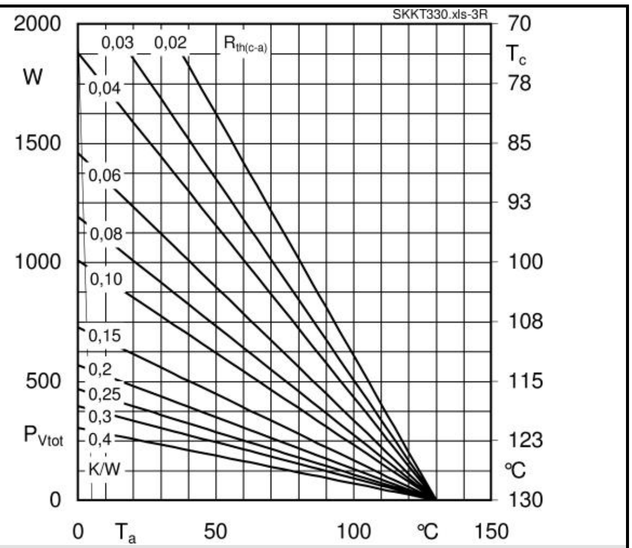

Fig. 3R Power dissipation of two modules vs. case temp.

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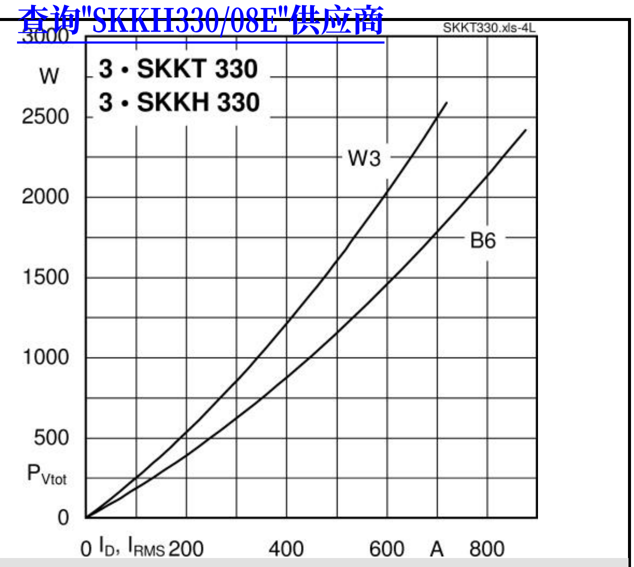

Fig. 4L Power dissipation of three modules vs. direct and rms current

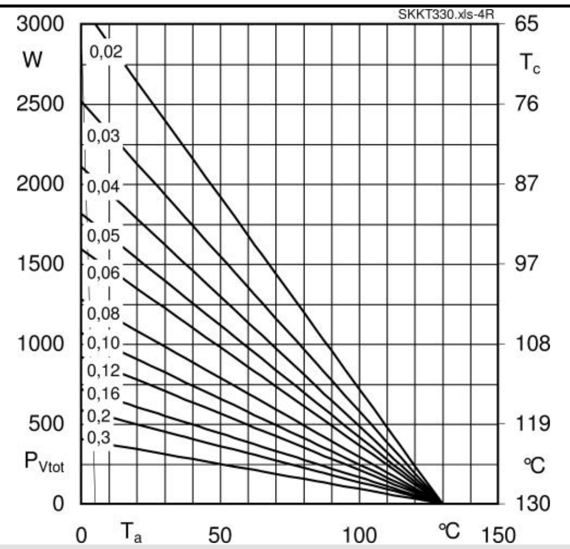

Fig. 4R Power dissipation of three modules vs. case temp.

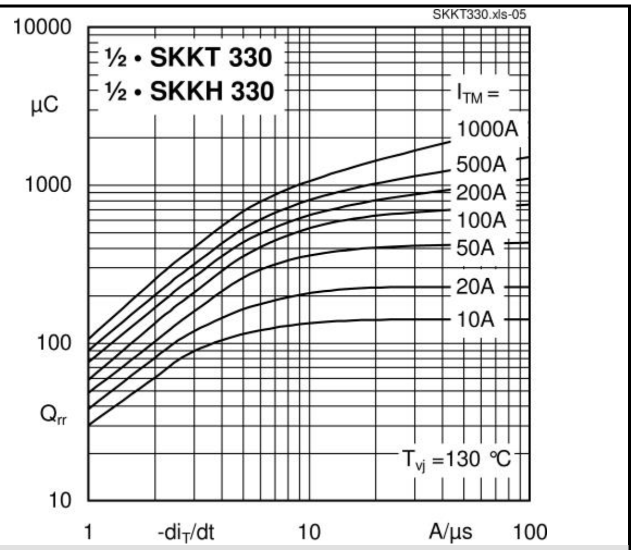

Fig. 5 Recovered charge vs. current decrease

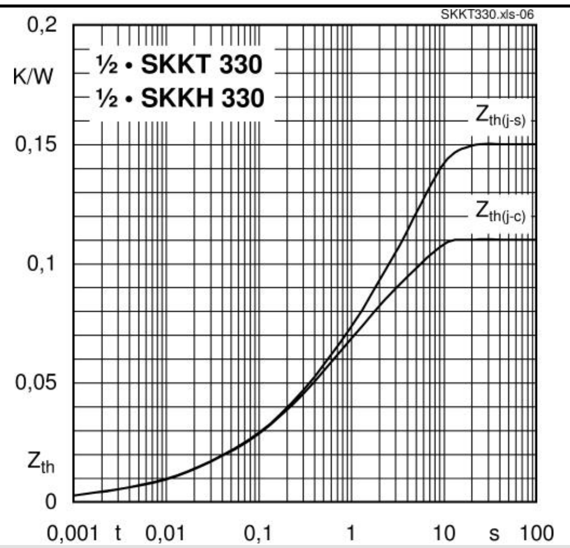

Fig. 6 Transient thermal impedance vs. time

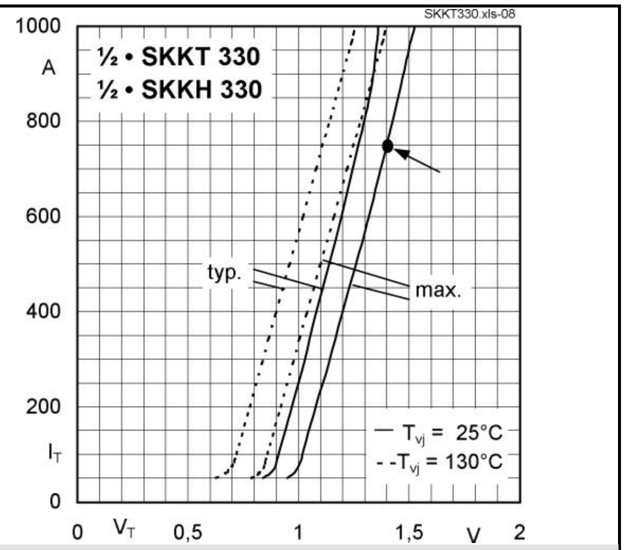

Fig. 7 On-state characteristics

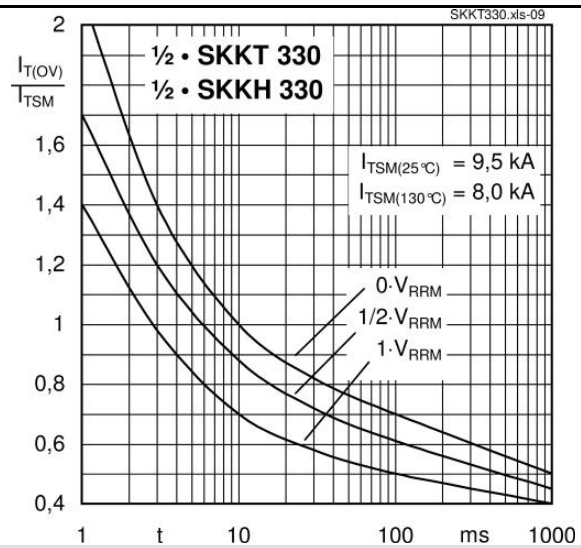

Fig. 8 Surge overload current vs. time

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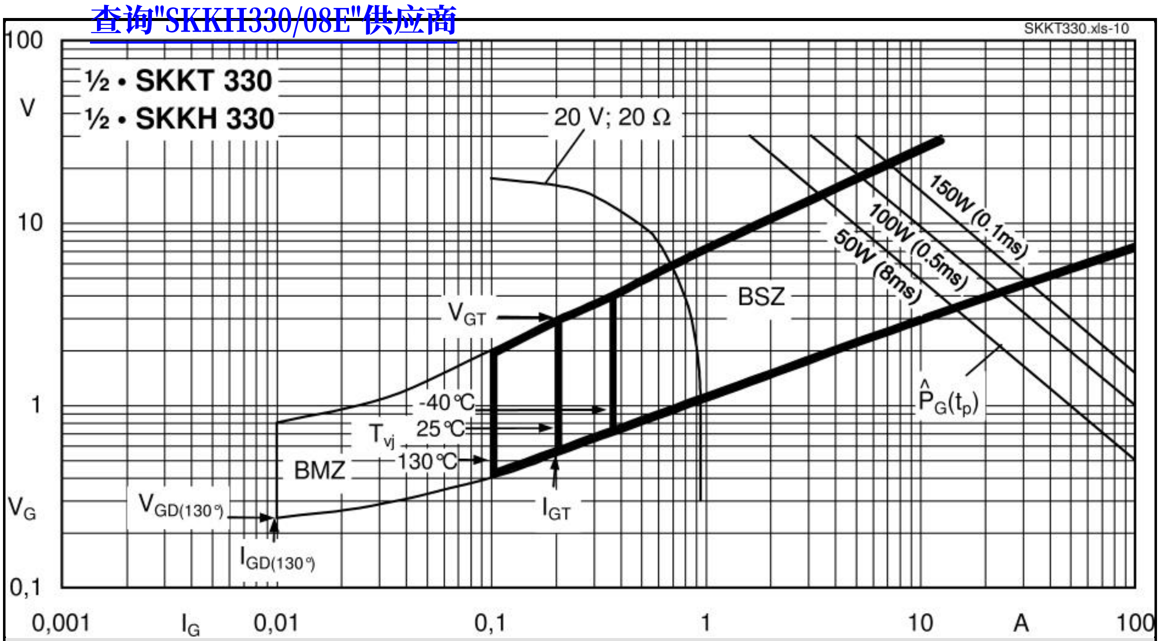
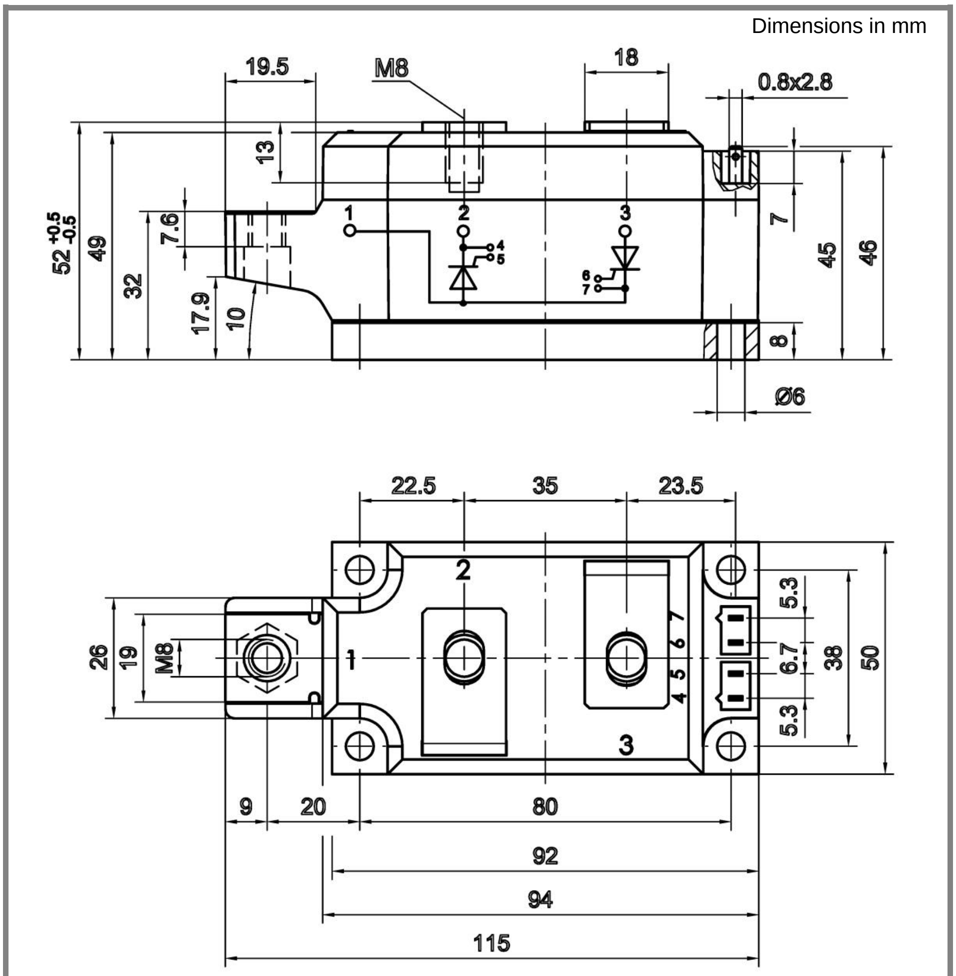
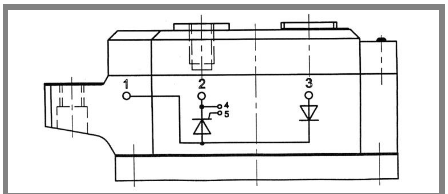


Fig. 9 Gate trigger characteristics



Case A 73b (SKKT)


Case A 76b SKKH

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